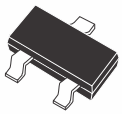
CMPT3640

PNP SILICON TRANSISTOR

Central Semiconductor Corp.™



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT3640 type is an PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for saturated switching applications.
Marking code is C2J.

MAXIMUM RATINGS (T_A=25°C)

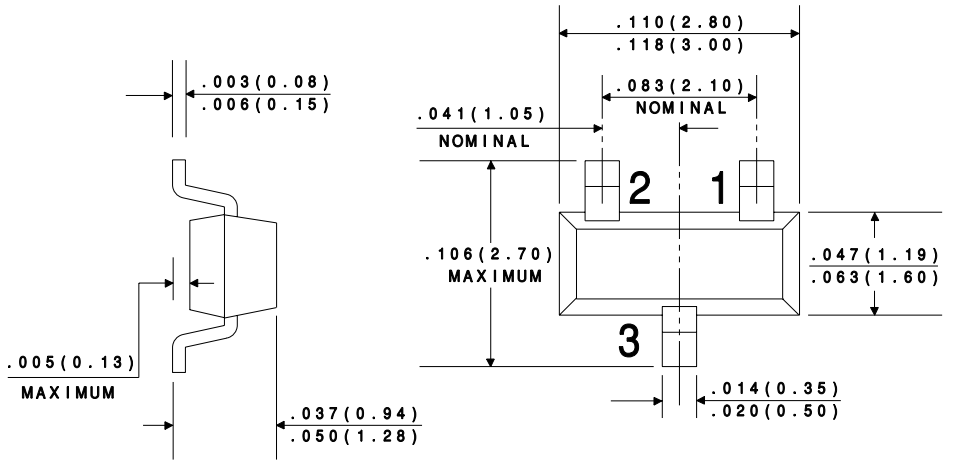
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	12	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	4.0	V
Collector Current	I_C	80	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CES}	V_{CE}=6.0V		10	nA
I_{CES}	V_{CE}=6.0V, T_A=65°C		10	µA
I_B	V_{CE}=6.0V, V_{EB}=0		10	nA
BV_{CBO}	I_C=100µA	12		V
BV_{CEO}	I_C=10mA	12		V
BV_{EBO}	I_E=100µA	4.0		V
$V_{CE(SAT)}$	I_C=10mA, I_B=1.0mA		0.20	V
$V_{CE(SAT)}$	I_C=50mA, I_B=5.0mA		0.60	V
$V_{CE(SAT)}$	I_C=10mA, I_B=1.0mA, T_A=65°C		0.25	V
$V_{BE(SAT)}$	I_C=10mA, I_B=0.5mA	0.75	0.95	V
$V_{BE(SAT)}$	I_C=10mA, I_B=1.0mA	0.80	1.00	V
$V_{BE(SAT)}$	I_C=50mA, I_B=5.0mA		1.50	V
h_{FE}	V_{CE}=0.3V, I_C=10mA	30	120	

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	V_{CE}=1.0V, I_C=50mA	20		
f_T	V_{CE}=5.0V, I_C=10mA, f=100MHz	500		MHz
C_{ob}	V_{CB}=5.0V, I_E=0, f=1.0MHz		3.5	pF
C_{ib}	V_{BE}=0.5V, I_C=0, f=1.0MHz		3.5	pF
t_d	V_{CC}=6.0V, V_{BE}=1.9, I_C=50mA, I_{B1}=5.0mA		10	ns
t_r	V_{CC}=6.0V, V_{BE}=1.9, I_C=50mA, I_{B1}=5.0mA		30	ns
t_s	V_{CC}=6.0V, I_C=50mA, I_{B1}=I_{B2}=5.0mA		20	ns
t_f	V_{CC}=6.0V, I_C=50mA, I_{B1}=I_{B2}=5.0mA		12	ns
t_{on}	V_{CC}=6.0V, V_{BE}=1.9, I_C=50mA, I_{B1}=5.0mA		25	ns
t_{on}	V_{CC}=1.5V, I_C=10mA, I_{B1}=0.5mA		60	ns
t_{off}	V_{CC}=6.0V, V_{BE}=1.9, I_C=50mA, I_{B1}=5.0mA		35	ns
t_{off}	V_{CC}=1.5V, I_C=10mA, I_{B1}=I_{B2}=0.5mA		75	ns

All dimensions in inches (mm).



LEAD CODE:

1) BASE
2) EMITTER
3) COLLECTOR